



IFJ

Docket No. TS02-262CIP (24061.480)
Customer No. 42717

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	Tien-J Bao, et al.	§	Docket No.:	TS02-262CIP
		§		(24061.480)
Serial No.:	10/808,801	§		
		§	Examiner:	To Be Determined
Filing Date:	March 25, 2004	§		
		§	Art Unit:	2834
For:	Method for Forming Openings	§		
	in Low-K Dielectric Layers	§	Conf. No.:	6033
		§		

PRELIMINARY AMENDMENT

Commissioner For Patents
PO Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Prior to the initial examination on the merits, please amend the above-captioned application as follows:

Amendments to the Specification begin on page 2 of this paper.

Remarks begin on page 3 of this paper.